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Amendment and/or Response  
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#### REMARKS/DISCUSSION OF ISSUES

##### **New Claims**

Upon entry of the present amendment, claims 24-39 are pending in the present application. Claims 24 and 32 are the independent claims. It is respectfully submitted that these claims add no new matter, as the features includes can be determined from the application as filed, for example within the details of Figs. 2(d) and 3(d).

##### **Rejections**

Claims 20 and 22 were rejected under 35 U.S.C. §112, second paragraph. This rejection is moot in view of the present amendment.

Claims 17 and 19-23 were rejected under 35 U.S.C. § 102(b) as being anticipated in view of Son (U.S. Patent 6,064,096). These claims have been cancelled. However, as the applied art may relate to the new claims, applicant offers the following remarks.

The establishment of a *prima facie* case of anticipation requires that all of the elements of a claim be found in the prior art. It follows that if a single element of a claim is missing from the prior art, a *prima facie* case of anticipation cannot be properly established.

Claim 24 is drawn to a MOS transistor, and features:  
"*...metallic silicide layers respectively formed on said source heavily doped regions and said drain heavily doped regions, said metallic silicide layers being in contact with said sidewalls and said isolation regions, and extending onto said isolation regions,...*"

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It is respectfully submitted that at least this feature is not disclosed by Son. To wit, Son includes a metal silicide layer 53, but this metal silicide layer does not extend onto the field region 42. As such, the applied reference to Son lacks at least the disclosure of one of the features of claim 24, and cannot serve to establish a *prima facie* case of anticipation. For at least this reason, new claim 24, and the claims that depend therefrom are allowable over the applied art.

Similarly, claim 32 is drawn to a semiconductor device including MOS transistors, and includes the features:  
"*...wherein each of said source regions has a source lightly doped region and a source heavily doped drain region, wherein an impurity concentration of said source lightly doped region is lower than an impurity concentration of said source heavily doped region, wherein the source lightly doped region is formed below one of said sidewalls, and wherein said heavily doped region is disposed between said source lightly doped region and one of said isolation regions;*

*wherein each of said drain regions has a drain lightly doped region and a drain heavily doped region, wherein an impurity concentration of said drain lightly doped region is lower than an impurity concentration of said drain heavily doped region, wherein the drain lightly doped region is formed below another of said sidewalls, and wherein said heavily doped drain region is disposed between said drain lightly doped region and said isolation region...*"

It is respectfully submitted that at least these features are not disclosed by Son. To wit, Son does include the p-halo

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regions 54 and the p- LD regions 55 on the PMOS structure. However, the lightly doped regions do not extend beneath the gate insulating film 43. As such, because the reference to Son lacks the teaching of at least one of the features of independent claim 32, the applied reference cannot serve to establish a prima facie case of anticipation. Accordingly, claim 26 and the claims that depend therefrom are allowable over the applied art for at least the specified reasons.

#### **Conclusion**

In view of the foregoing, applicant(s) respectfully request(s) that the Examiner withdraw the rejections of record, allow all the pending claims, and find the application to be in condition for allowance. If any points remain in issue that may best be resolved through a personal or telephonic interview, the Examiner is respectfully requested to contact the undersigned at the telephone number listed below.

Petition is hereby made for a two-month extension of time as provided under 37 C.F.R. § 1.136(a), extending the period of response from June 28, 2003 to August 28, 2003. Permission is hereby given to charge Deposit Account Number 50-0238 for the required fee under 37 C.F.R. § 1.17.

In the event that there are any outstanding matters remaining in the present application, the Examiner is invited to contact William S. Francos, Esq. (Reg. No. 38,456) at (610) 375-3513 to discuss these matters.

If necessary, the Commissioner is hereby authorized in this, concurrent, and further replies to charge payment or credit any overpayment to Deposit Account Number 50-0238 for any additional fees under 37 C.F.R. §1.16 or under 37 C.F.R. §1.17.

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Respectfully submitted on behalf of:  
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Reg. No. 38,456

**FAX RECEIVED****AUG 29 2003****GROUP 2800**

Date: August 28, 2003

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